# SLOVENSKI STANDARD

# SIST EN 60758:2005

december 2005

Sintetični kremenčev kristal – Specifikacije in vodilo za uporabo (IEC 60758:2004)

Synthetic quartz crystal – Specifications and guide to the use (IEC 60758:2004)

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# EUROPEAN STANDARD

EN 60758

### NORME EUROPÉENNE

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### Synthetic quartz crystal – Specifications and guide to the use (IEC 60758:2004)

Quartz synthétique -Spécifications et guide d'utilisation (CEI 60758:2004)

Synthetischer Quarzkristall -Festlegungen und Leitfaden für die Anwendung (IEC 60758:2004)

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# CENELEC

European Committee for Electrotechnical Standardization Comité Européen de Normalisation Electrotechnique Europäisches Komitee für Elektrotechnische Normung

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#### Foreword

The text of document 49/696/FDIS, future edition 3 of IEC 60758, prepared by IEC TC 49, Piezoelectric and dielectric devices for frequency control and selection, was submitted to the IEC-CENELEC parallel vote and was approved by CENELEC as EN 60758 on 2005-02-01.

The following dates were fixed:

<ul> <li>latest date by which the EN has to be implemented at national level by publication of an identical national standard or by endorsement</li> </ul>	(dop)	2005-11-01
<ul> <li>latest date by which the national standards conflicting with the EN have to be withdrawn</li> </ul>	(dow)	2008-02-01

Annex ZA has been added by CENELEC.

#### **Endorsement notice**

The text of the International Standard IEC 60758:2004 was approved by CENELEC as a European Standard without any modification. I ANDARD PREVIEW

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### Annex ZA

#### (normative)

# Normative references to international publications with their corresponding European publications

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE Where an international publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

Publication	Year	<u>Title</u>	<u>EN/HD</u>	Year
IEC 60068-1	1988	Environmental testing Part 1: General and guidance	EN 60068-1 1)	1994
IEC 60122-1	2002	Quartz crystal units of assessed quality Part 1: Generic specification	EN 60122-1	2002
IEC 60410	1973	Sampling plans and procedures for inspection by attributes	-	-
IEC 61994	Series	Piezoelectric and dielectric devices for F frequency control and selection - Glossary and ards.iteh.ai)	W	-

<sup>1)</sup> EN 60068-1 includes corrigendum October 1988 + A1:1992 to IEC 60068-1.

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# INTERNATIONAL STANDARD



Third edition 2004-12

### Synthetic quartz crystal – Specifications and guide to the use

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#### SYNTHETIC QUARTZ CRYSTAL – SPECIFICATIONS AND GUIDE TO THE USE

#### FOREWORD

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International Standard IEC 60758 has been prepared by IEC technical committee 49: Piezoelectric and dielectric devices for frequency control and selection.

This third edition cancels and replaces the second edition, published in 1993, and its amendments 1 (1997) and 2 (2001).

This edition includes the following significant technical changes with respect to the previous edition:

- a) it combines the information given in the second edition and in the amendments into one single document;
- b) it adds the infrared absorbance alpha value compensation method as Annex E.

The text of this standard is based on the following documents:

FDIS	RVD
49/696/FDIS	49/701/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

The committee has decided that the contents of this publication will remain unchanged until the maintenance result date indicated on the IEC web site under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

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#### SYNTHETIC QUARTZ CRYSTAL – SPECIFICATIONS AND GUIDE TO THE USE

#### 1 Scope

This International Standard applies to synthetic quartz single crystals intended for manufacturing piezoelectric elements for frequency control and selection.

#### 2 Normative references

The following referenced documents are indispensable for the application of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60068-1:1988, Environmental testing – Part 1: General and guidance

IEC 60122-1:2002, Quartz crystal units of assessed quality – Part 1: Generic specification.

IEC 60410:1973, Sampling plans and procedures for inspection by attributes

IEC 61994 (all parts), Piezoelectric and dielectric devices for frequency control and selection – Glossary

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#### **3 Terms and definitions**ds.iteh.ai/catalog/standards/sist/fcaa3be9-1cd8-4c89-b3d4-8188eb3a4aa6/sist-en-60758-2005

For the purposes of this document, the following terms and definitions, as well as those given in IEC 61994, apply.

#### 3.1

#### hydrothermal crystal growth

literally, crystal growth in the presence of water, elevated temperatures and pressures by a crystal growth process believed to proceed geologically within the earth's crust. The industrial synthetic quartz growth processes utilize alkaline water solutions confined within autoclaves at supercritical temperatures (330 °C to 400 °C) and pressures (700 to 2 000 atmospheres). The autoclave is divided into two chambers: the dissolving chamber, containing raw quartz chips at the higher temperature; the growing chamber, containing cut seeds at the lower temperature (see 7.1.2)

#### 3.2

synthetic quartz crystal (also known as cultured quartz crystal)

single crystal of  $\alpha$  quartz grown by the hydrothermal method. The crystal is of either handedness and in the as-grown condition

#### 3.2.1

#### as-grown synthetic quartz crystal

single crystal quartz grown hydrothermally. As-grown refers to the state of processing and indicates a state prior to whatever treatment might occur after growth, excluding quality control operations

#### 3.2.2

#### as-grown Y-bar

crystals which are produced using seed with the largest dimension in the Y-direction

#### 3.2.3

#### as-grown Z-bar

crystals in which the Z-grown sector is much larger that the X-grown sector. The relative size of the growth sector is controlled by the X-dimension of the seed

#### 3.3

#### synthetic quartz crystal batch

synthetic quartz crystals grown at the same time in one autoclave

#### 3.4

#### seed

rectangular parallelepiped quartz plate or bar to be used as a nucleus for crystal growth

#### 3.5

#### growth zones

regions of a synthetic quartz crystal resulting from growth along different crystallographic directions (see Figure 1)

#### 3.6

#### orientation of a synthetic quartz crystal

orientation of its seed with respect to the orthogonal axes specified in 3.7

#### 3.7

#### orthogonal axial system of a guartz crystal 2 7 1 PREVIEW

3.7.1

#### axial system for quartz illustrated in Figure 2rds. iteh.ai)

NOTE The Z-cut seed may be oriented at an angle of less than 20° to the Y-axis, in this case the axial system becomes X, Y', Z'. <u>SIST EN 60758:2005</u>

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#### 3.7.2 AT-cut plate

rotated Y-cut crystal plate oriented at an angle of about +35° around the X-axis or about -3° from the z (minor rhombohedral)-face as shown in Figure 3

#### 3.7.3

#### z (minor rhombohedral)-cut plate

crystal plate parallel to the z (minor rhombohedral)-face as shown in Figure 3a

#### 3.7.4

#### X-cut plate

crystal plate perpendicular to the X-axis as shown in Figure 3b

#### 3.7.5

#### Y-cut plate

crystal plate perpendicular to the Y-axis as shown in Figure 3b

#### 3.7.6

#### Z-cut plate

crystal plate perpendicular to the Z-axis as shown in Figure 3b

#### 3.8

#### dimensions

dimensions pertaining to growth on Z-cut seed rotated less than 20° from the Y-axis

#### gross dimensions

maximum dimensions along the X-, Y-, or Y'-, and Z- or Z'-axes measured along the X-, Y'- and Z'-axes

#### 3.8.1.1

#### effective Z-dimension

as-grown effective Z dimension defined as the minimum measure in the Z ( $\Theta = 0^{\circ}$ ) or Z' direction in usable Y or Y' area of an as-grown crystal and described by Z<sub>eff</sub> ,as shown in Figure 1

#### 3.8.1.2

#### minimum Z-dimension

minimum distance from seed surface to Z-surface described by  $Z_{min}$  as shown in Figure 1d

#### 3.8.2

dimensions pertaining to growth on a Z-cut seed rotated more than 20° from the X-axis (under consideration)

#### 3.9

#### inclusions

any foreign material within a synthetic quartz crystal, visible by examination of scattered light from a bright source with the crystal immersed in a refractive index-matching liquid. A particularly common inclusion is the mineral acmite (sodium iron silicate)

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#### 3.9.1 seed veil

seed veil array of inclusions or voids at the surface of the seed upon which a crystal has been grown

#### 3.9.2

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roughly cylindrical void that is present along dislocation line after etching a quartz crystal

#### 3.10

#### dopant

any additive used in the growth process which may change the crystal habit, chemical composition, physical or electrical properties of the synthetic quartz batch

#### 3.11

#### pre-dimensioned bar

any bar whose as-grown dimensions have been altered by sawing, grinding, lapping, etc., to meet a particular dimensional requirement

#### 3.12

#### impurity concentration

concentration of impurities relative to silicon atoms

#### 3.13

#### dislocations

linear defects in the crystal due to misplaced planes of atoms

#### 3.14

#### etch channel

roughly cylindrical void present along a dislocation line after etching a test wafer prepared from a quartz crystal

#### 3 15

#### autoclave

vessel for the high-pressure high-temperature condition required for growth of synthetic quartz crystal

#### 3.16

#### right-handed guartz or left-handed guartz

handedness of quartz crystal as determined by observing the sense of handedness of the optical rotation in the polarized light. Right-handed quartz is the crystal of dextrorotatory and left-handed guartz is the crystal of levorotary

#### 3.17

twins

twins follow laws of crystallography relating symmetrically to specific faces or axes.

The following types have been identified in synthetic guartz crystals:

a) Electrical twins

Quartz crystal in which regions with the common Z-axis exist showing a polarity reversal of the electrical X-axis.

b) Optical twins

Quartz crystal in which regions with the common Z-axis exhibit handedness reversal of the optical Z-axis

#### 3.18

### **iTeh STANDARD PREVIEW**

infrared absorption coefficient  $\alpha$ -value coefficient (referred to as the  $\alpha$ -value) established by determining the relationship between absorption of two wavelengths: one with minimal absorption due to OH impurity, the other with high absorption due to presence of OH impurities in the crystal lattice. The OH impurity creates mechanical loss interesonatorsicandaits presencestisacorrelated to the presence of other loss-inducting impurities. The  $\alpha$ -value is a measure of  $\Theta$  H concentration and is correlated with expected mechanical losses due to material impurities. The infrared absorption coefficient  $\alpha$ -value is determined using the following equation:

$$\alpha = \frac{1}{t} \log \frac{T_1}{T_2}$$

where

- $\alpha$  is the infrared absorption coefficient;
- t is the thickness of Y-cut sample, in centimetres;
- $T_1$  is the per cent transmission at a wave number of 3 800 cm<sup>-1</sup> or 3 979 cm<sup>-1</sup>;

 $T_2$  is the per cent transmission at a wave number of 3 410 cm<sup>-1</sup>, 3 500 cm<sup>-1</sup> or 3 585 cm<sup>-1</sup>.

#### 3.19

#### lumbered synthetic quartz crystal

synthetic quartz crystal whose X- and Z- or Z'- surfaces in the as-grown condition have been processed flat and parallel by sawing, grinding, lapping, etc., to meet specified dimensions and orientation

3 19 1

### **lumbered Y-bar**

quartz bars which are lumbered from an as-grown Y-bar

3.19.2 **lumbered Z-bar** quartz bars which are lumbered from an as-grown Z-bar